



# STB75NE75

## N - CHANNEL 75V - 0.01 $\Omega$ - 75A - D<sup>2</sup>PAK STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB75NE75	75 V	<0.013 $\Omega$	75 A

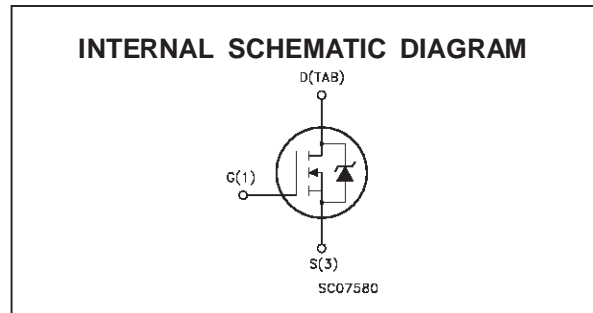
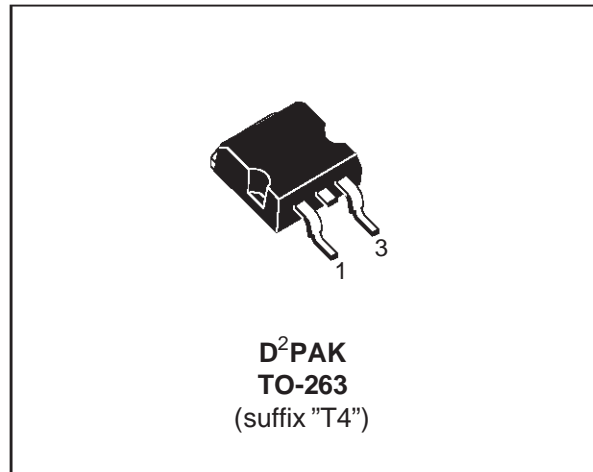
- TYPICAL R<sub>DS(on)</sub> = 0.01  $\Omega$
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- DC MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	75	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	75	V
V <sub>GS</sub>	Gate-source Voltage	$\pm 20$	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	75	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	53	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	300	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	160	W
	Derating Factor	1.06	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	7	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub>  $\leq$  75 A, di/dt  $\leq$  300 A/ $\mu$ S, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>

## STB75NE75

### THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.94	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.5	$^{\circ}C/W$
$T_I$	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max)	75	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 30 V$ )	500	mJ

### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	75			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 V$			$\pm 100$	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 5 V$ $I_D = 37.5 A$		10	13	m $\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	75			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 37.5 A$		40		S
$C_{iss}$	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		5300		pF
$C_{oss}$	Output Capacitance			850		pF
$C_{rss}$	Reverse Transfer Capacitance			310		pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 40\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		32		ns
$t_r$	Rise Time			130		ns
$Q_g$	Total Gate Charge	$V_{DD} = 60\text{ V}$ $I_D = 75\text{ A}$ $V_{GS} = 10\text{ V}$		150	200	nC
$Q_{gs}$	Gate-Source Charge			30		nC
$Q_{gd}$	Gate-Drain Charge			62		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 40\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, see fig. 3)		150		ns
$t_f$	Fall Time			45		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 60\text{ V}$ $I_D = 75\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Inductive Load, see fig. 5)		35		ns
$t_f$	Fall Time			60		ns
$t_c$	Cross-over Time			100		ns

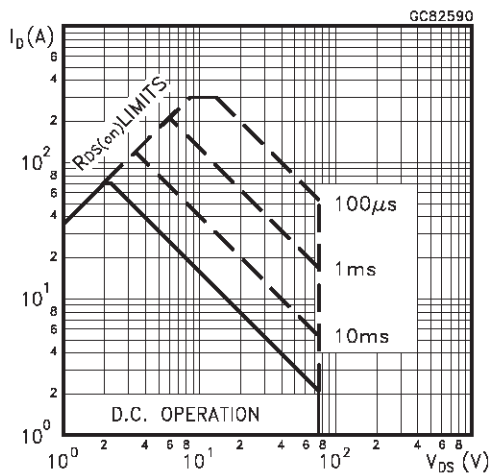
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				75	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				300	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 75\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 75\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		130		ns
$Q_{rr}$	Reverse Recovery Charge			0.6		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			9		A

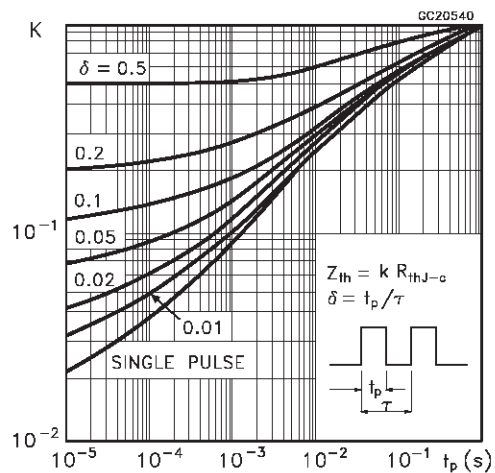
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

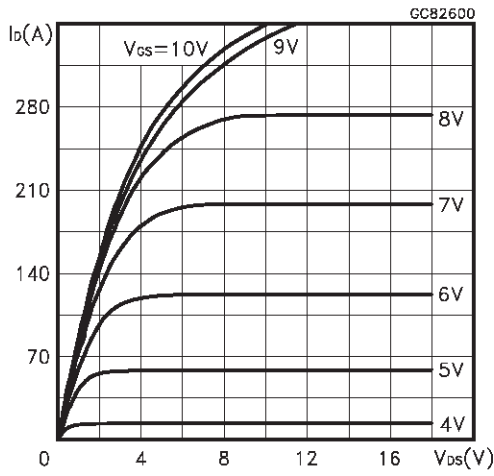
**Safe Operating Area**



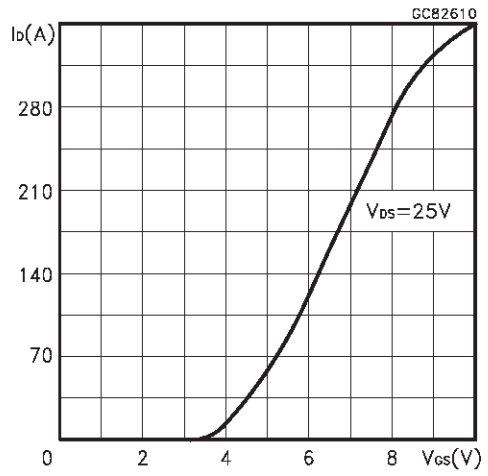
**Thermal Impedance**



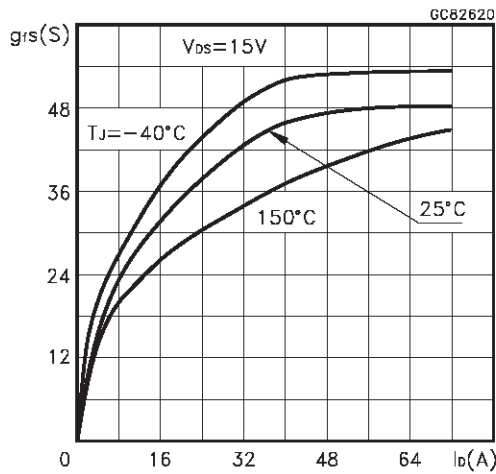
Output Characteristics



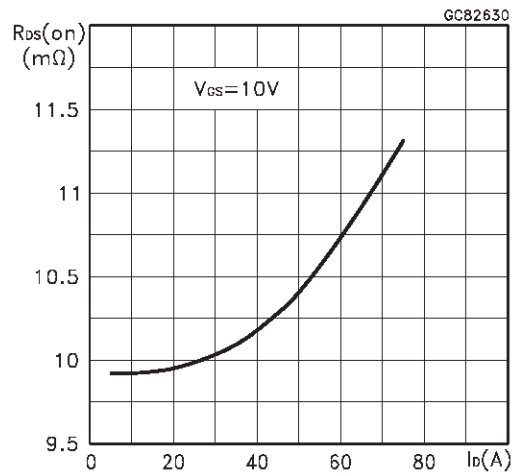
Transfer Characteristics



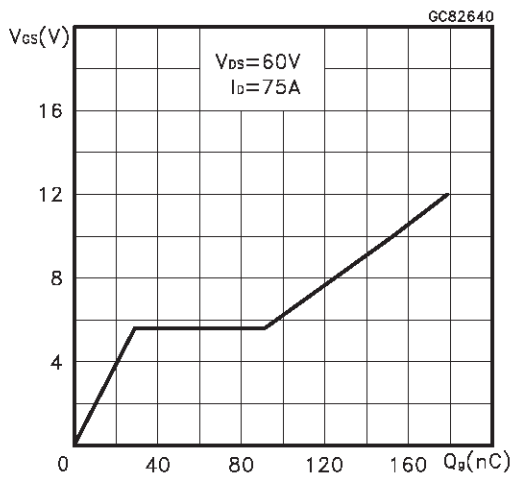
Transconductance



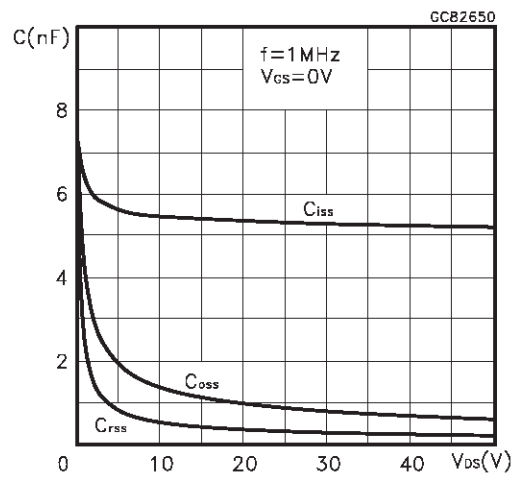
Static Drain-source On Resistance



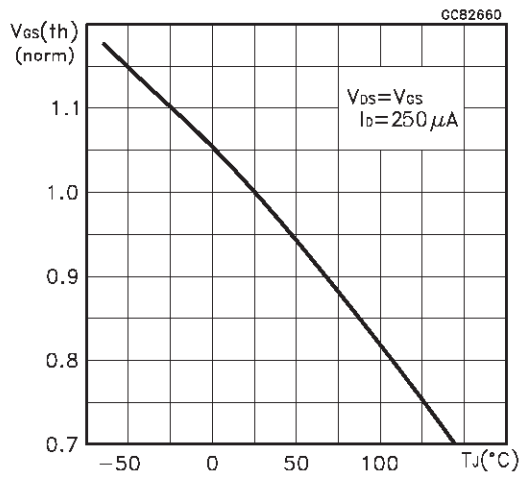
Gate Charge vs Gate-source Voltage



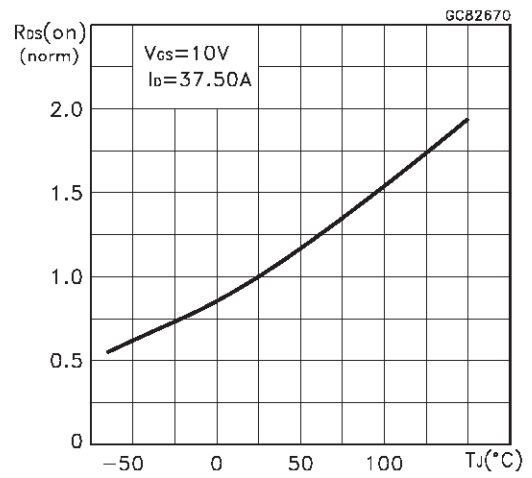
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

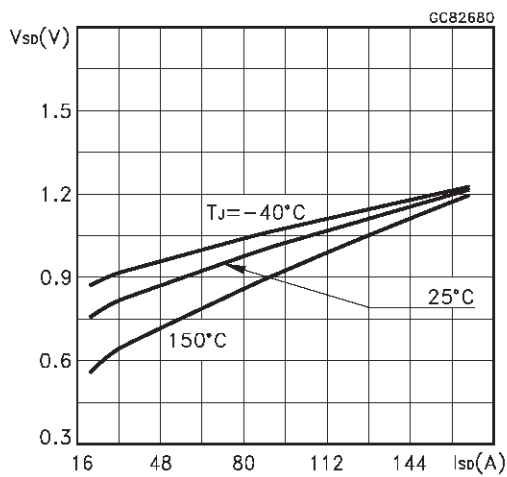


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

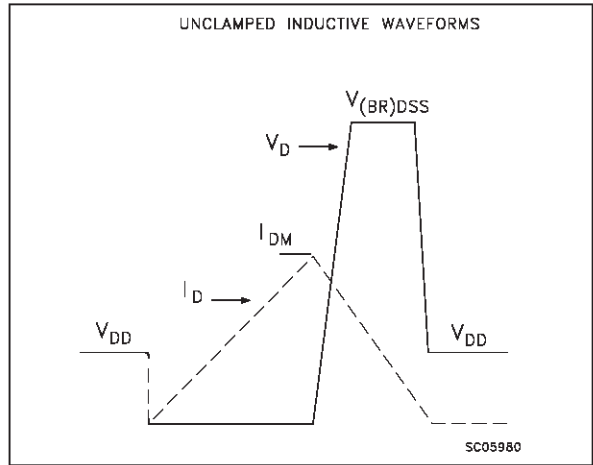


Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

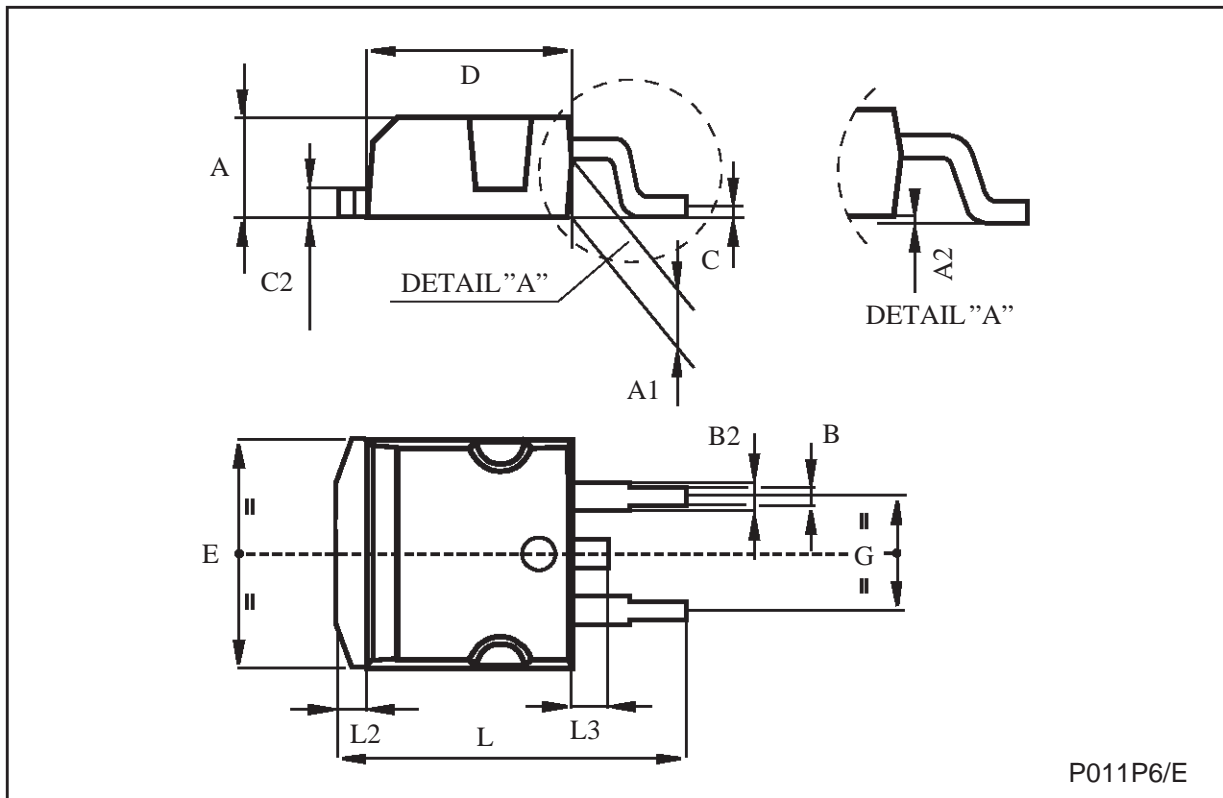


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.4	0.393		0.409
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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